



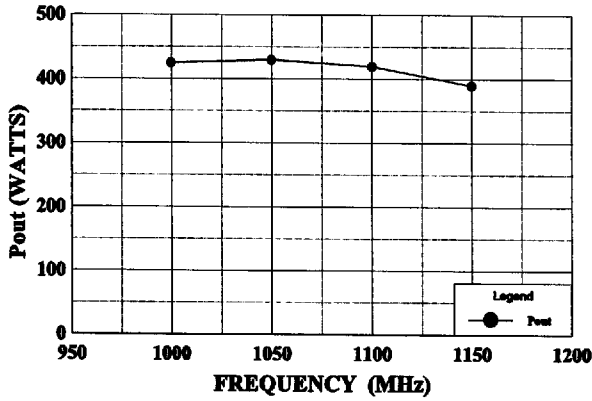


**GHz TECHNOLOGY**  
RF-MICROWAVE SILICON POWER TRANSISTORS

**DME 375**

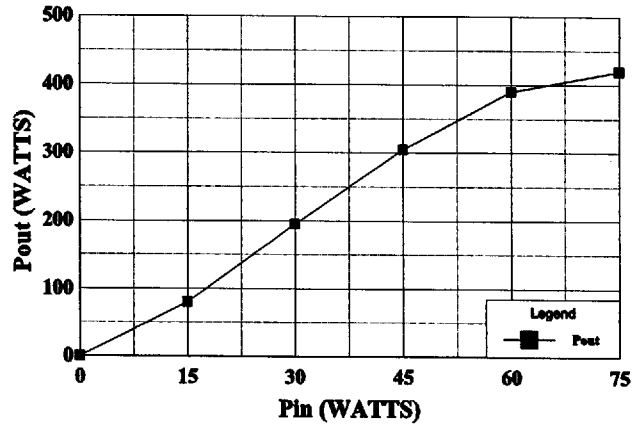
**POWER OUTPUT vs FREQUENCY**

Vcc = 50 V, Pin = 65 W



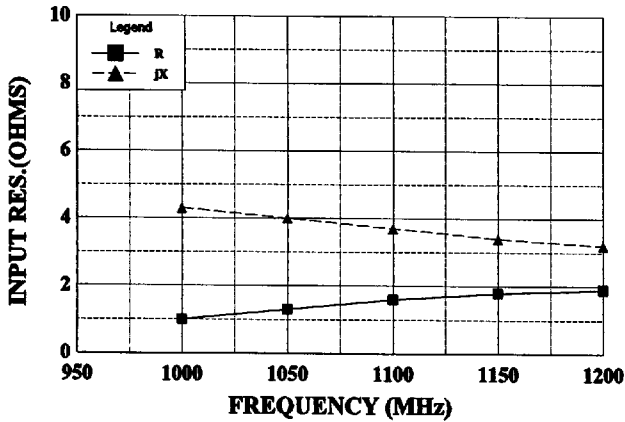
**Pout vs Pin**

Vcc=50V, f=1090 MHz



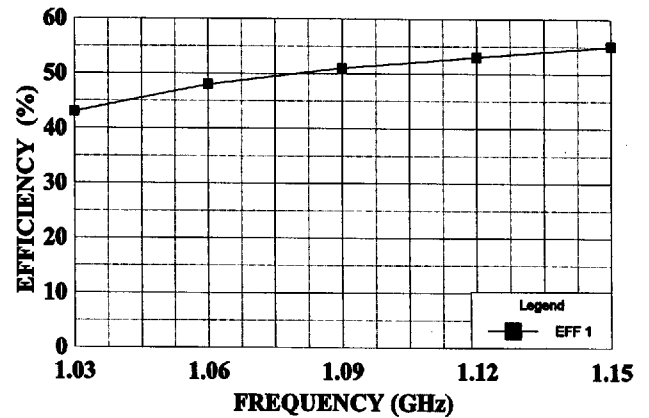
**SERIES INPUT IMPEDANCE vs FREQUENCY**

Vcc = 50 V, Po = 375 W



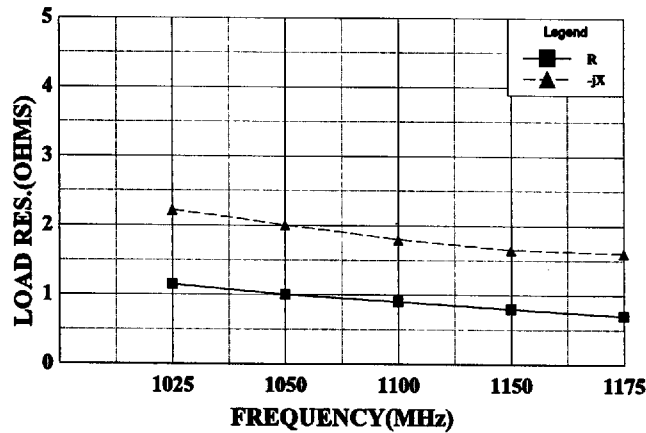
**COLLECTOR EFFICIENCY**

Vcc = 50 V, Pin = 75 W



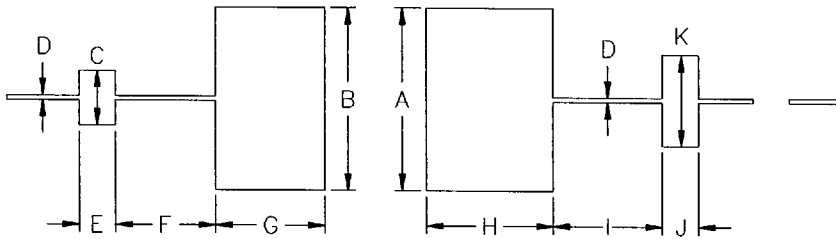
**SERIES LOAD IMPEDANCE vs FREQUENCY**

Vcc = 50 V, Po = 375 W



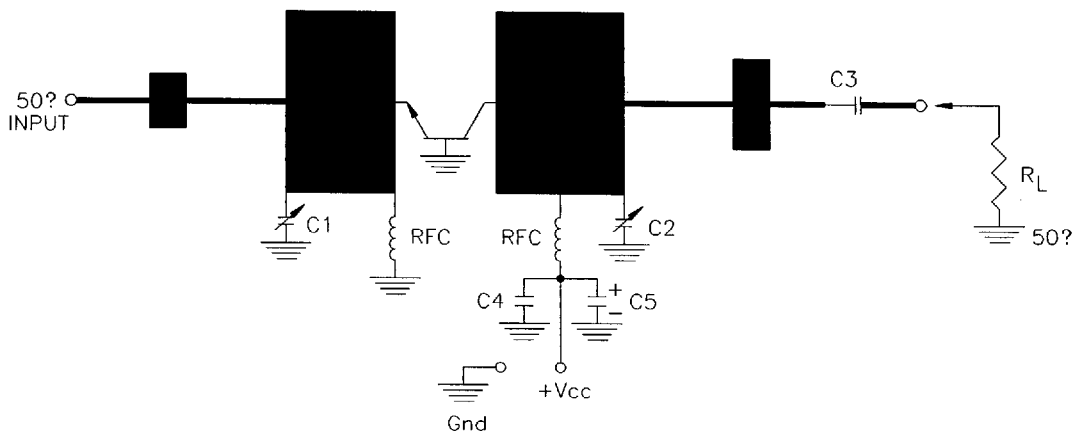
REVISIONS

ZONE	REV	DESCRIPTION	DATE	APPROVED
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DIM	INCHES
A	1.000
B	1.000
C	.300
D	.025
E	.200
F	.550
G	.600
H	.700
I	.600
J	.200
K	.500

DME 375 / TPR 400 TEST FIXTURE  
1025-1150 MHz/1030/1090 MHz - TEST AMPLIFIER (FIG1)



- MICROSTRIP LINE: DUROID, 10 MIL DIELECTRIC D 5880, er=2.33
- C1, C2 - 0.6-6pf VAR. CAP.
- C3, C4 - 82 pf CHIP
- C5 - 200 MFD CAP.

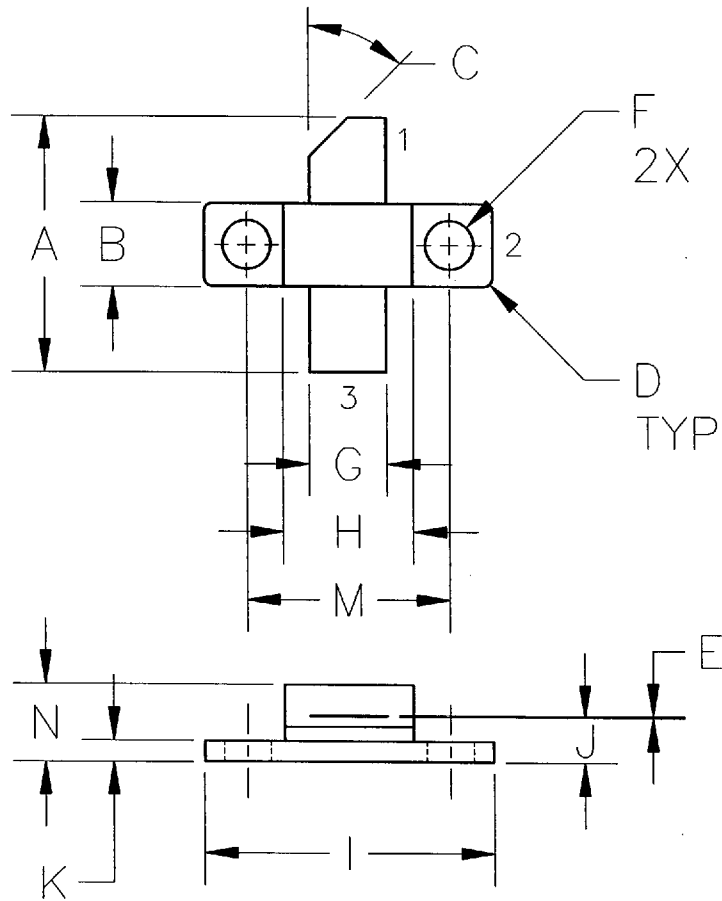


**GHz TECHNOLOGY**

CAGE OPJR2	DWG NO. DME 375 / TPR 400	REV -
SCALE 1/1	SHEET	

REVISIONS

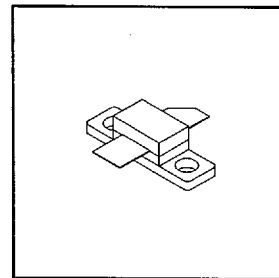
ZONE	REV	DESCRIPTION	DATE	APPROVED
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DIM	MILLIMETER	TOL	INCHES	TOL
A	17.78	.76	.700	.030
B	5.84	.13	.230	.005
C	45°	5°	45°	5°
D	0.63R	.13	.025R	.005
E	.13	.02	.005	.001
F	3.30 DIA	.13	.130 DIA	.005
G	5.46	.13	.215	.005
H	9.14	.13	.360	REF
I	20.32	.13	.800	.005
J	3.17	.25	.125	.010
K	1.52	.13	.060	.005
M	14.22	.13	.560	.005
N	5.46	REF	.215	REF

STYLE 1:  
 PIN1 = COLLECTOR  
 2 = BASE  
 3 = EMITTER

STYLE 2:  
 PIN1 = COLLECTOR  
 2 = EMITTER  
 3 = BASE



CAGE OPJR2	DWG NO. 55CX	REV A
SCALE 2/1	SHEET	